

**IN THE CLAIMS:**

Please cancel claims 20, 35 and 36 without prejudice.

Kindly amend claims 17-19, 21-34 and 37-50 as follows:

Claims 1-16 (Canceled)

17. (Twice amended) ~~A material comprising an organic die bonding film having a~~ peel strength of 0.5 kgf/(5 mm x 5 mm chip) or higher when a semiconductor has been bonded to a support member with said ~~film material~~ under conditions of 100-230°C temperature and pressure of 0.1-30 gf/mm<sup>2</sup>, wherein said film comprises an organic material selected from the group consisting of epoxy resin, silicone resin, acrylic resin and polyimide resin.

18. (Twice amended) ~~A material comprising an organic die bonding film according to claim 19 having the property of bonding a semiconductor chip to a support member under conditions of 100-230°C temperature and pressure of 0.1-30 gf/mm<sup>2</sup>, and having a saturation moisture absorption of 1.0% by volume or less.~~

19. (Twice amended) ~~A material comprising an organic die-bonding single layer~~ film having the property of bonding a semiconductor chip to a support member under conditions of 100-230°C temperature and pressure of 0.1-30 gf/mm<sup>2</sup>, and having a modulus of elasticity of 10 MPa or less at a temperature of 250°C, wherein the film comprises an organic material selected from the group consisting of epoxy resin, silicone resin, acrylic resin and polyimide resin.

20. (Canceled)

21. (Twice amended) A ~~material comprising an organic die-bonding film according to claim 19~~ having the property of bonding a semiconductor chip to a support member under conditions of 100–230°C temperature and pressure of 0.1–30 gf/mm<sup>2</sup>, having a residual volatile component in an amount of not more than 3.0% by weight.

22. (Twice amended) A ~~material comprising an organic die-bonding film according to claim 21~~ having the property of bonding a semiconductor chip to a support member under conditions of 100–230°C temperature and pressure of 0.1–30 gf/mm<sup>2</sup>, having water absorption of 1.5% by volume or less.

23. (Amended) A film ~~material~~ according to claim 17, wherein the ~~comprising an organic die-bonding film~~ has further having a modulus of elasticity of 10 Mpa or less at a temperature of 250°C.

24. (Amended) A film ~~material~~ according to claim 23, ~~comprising an organic die-bonding film further~~ having a water absorption of 1.5% by volume or less.

25. (Amended) A film ~~material~~ according to claim 23, ~~comprising an organic die-bonding film further~~ having a residual volatile component in an amount of not more than 3.0% by weight.

26. (Amended) A ~~film~~material according to claim 25, ~~comprising an organic die-bonding film further~~ having a saturation moisture absorption of 1.0% by volume or less.

27. (Amended) A ~~film~~material according to claim 26, ~~comprising an organic die-bonding film further~~ having a void volume of 10% or less in terms of voids present in the material and at an interface between said material and a support member at a stage where a semiconductor had been bonded to a support member by said material.

28. (Amended) A ~~film~~material according to claim ~~1720~~, wherein the film ~~has~~comprising an organic die-bonding film further having a water absorption of 1.5% by volume or less, ~~having a~~ saturation moisture absorption of 1.0% by volume or less, and ~~having a~~ modulus of elasticity of 10 MPa or less at a temperature of 250°C.

29. (Amended) A ~~film~~material according to claim ~~1720~~, wherein the film has ~~comprising an organic die-bonding film further~~ having a saturation moisture absorption of 1.0% by volume or less, ~~having and~~ a modulus of elasticity of 10 MPa or less at a temperature of 250°C, ~~and having a peel strength of 0.5 kgf/(5 mm x 5 mm chip) or higher.~~

30. (Amended) A ~~material comprising an organic die-bonding film~~ having the property of bonding a semiconductor chip to a support member under conditions of 100-250°C temperature and pressure of 0.1-30 gf/mm<sup>2</sup>, wherein the film has~~and having~~ a water absorption of 1.5% by volume or less, a saturation moisture absorption of 1.0% by volume or less, a modulus of elasticity of 10 MPa or less at a temperature of 250°C, a void volume of 10% or less in terms of voids present in the ~~film~~material and at an interface between said ~~film~~material and a support member at a stage where a semiconductor has been bonded to a

support member by said ~~film~~material, a peel strength of 0.5 kgf/(5 mm x 5 mm chip) or higher at a stage where a semiconductor has been bonded to a support member with said ~~film~~material, and a residual volatile component in an amount of not more than 3.0% by weight, wherein the film comprises an organic material selected from the group consisting of epoxy resin, silicone resin, acrylic resin and polyimide resin.

31. (Amended) A ~~film~~material according to claim 17, wherein the film isbeing a self-supporting film.

32. (Amended) A ~~film~~material according to claim 30, wherein the film isbeing a self-supporting film.

33. (Amended) A ~~film~~material according to claim 17, wherein the film hashaving a single layer structure.

34. (Amended) A ~~film~~material according to claim 30, wherein the film hasving a single layer structure.

35. (Canceled)

36. (Canceled)

37. (Amended) A ~~film~~material according to claim 17, wherein said ~~film~~ material is an organic material comprising a polyimide resin.

38. (Amended) A filmmaterial according to claim 30, wherein said film material is ~~an organic material comprising~~ a polyimide resin.

39. (Amended) A filmmaterial according to claim ~~31~~7, wherein said ~~material is~~ an ~~organic material comprising~~ a polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-dimethylphenyl)methane.

40. (Twice amended) A filmmaterial according to claim ~~31~~7, wherein said ~~material is an organic material comprising~~ a polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and 4,4'-diaminodiphenyl ether.

41. (Amended) A filmmaterial according to claim ~~31~~7, wherein said ~~material is~~ an ~~organic material comprising~~ a polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-diisopropylphenyl)methane.

42. (Amended) A filmmaterial according to claim ~~31~~7, wherein said ~~material is~~ an ~~organic material comprising~~ a polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and 2,2-bis[4-(4-aminophenoxy)phenyl] propane.

43. (Twice amended) A filmmaterial according to claim ~~31~~7, wherein said ~~material is an organic material comprising~~ a polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride), 1,10-(decamethylene)bis(trimellitate anhydride), and 2,2-bis[4-(4-aminophenoxy)phenyl] propane.

44. (Amended) A ~~filmmaterial~~ according to claim ~~31~~7, wherein said ~~material is~~ an organic material comprising a polyimide ~~is~~ synthesized from 1,10-(decamethylene)bis(trimellitate anhydride), and 2,2-bis[4-(4-aminophenoxy)phenyl] propane.

45. (Amended) A ~~filmmaterial~~ according to claim 17, wherein said ~~film material~~ is an organic material ~~further~~ comprising an epoxy resin.

46. (Amended) A ~~filmmaterial~~ according to claim ~~30~~17, wherein said ~~film material~~ is an organic material ~~further~~ comprising a polyimide resin and an epoxy resin.

47. (Amended) A ~~filmmaterial~~ according to claim ~~17~~35, further comprising a metal filler.

48. (Amended) A ~~filmmaterial~~ according to claim ~~30~~6, further comprising a metal filler.

49. (Amended) A ~~filmmaterial~~ according to claim ~~17~~35, made by a process comprising the steps of coating a varnish on a carrier film and peeling the die bonding ~~filmmaterial~~ from said carrier film.

50. (Amended) A ~~filmmaterial~~ according to claim ~~30~~6, made by a process comprising the steps of coating a varnish on a carrier film and peeling the die bonding ~~filmmaterial~~ from said carrier film.